

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A semiconductor device comprising:

a pixel TFT disposed in a pixel section; and

a driver circuit comprising a p-channel TFT and an n-channel TFT,
over a substrate,

wherein:

the p-channel TFT of the driver circuit comprises a channel forming region and a p-type impurity region of a fourth concentration that forms a source region or a drain region and is disposed in contact with the channel forming region;

the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which forms a LDD region that is disposed in contact with the channel forming region and partly overlaps a gate electrode, and an n-type impurity region of a third concentration which is disposed in the outside of the n-type impurity region of the first concentration and forms a source region or a drain region;

the pixel TFT comprises a channel forming region, an n-type impurity region of a second concentration which is disposed in contact with the channel forming region and forms a LDD region, and an n-type impurity region of the third concentration which is disposed in the outside of the n-type impurity region of the second concentration and forms a source region or a drain region and

a pixel electrode disposed in the pixel section has a light reflective surface, the pixel electrode is formed over an interlayer insulating film comprising an organic insulating material, and is connected to the pixel TFT through an opening formed in a protective insulating film comprising an inorganic insulating material disposed over a gate electrode of the pixel TFT and in the interlayer insulating film formed in contact with the protective insulating film.

3. (Amended) A semiconductor device having a liquid crystal sandwiched between a pair of substrates, wherein:

one of the substrates comprises a pixel TFT disposed in a pixel section and a p-channel TFT and an n-channel TFT of a driver circuit, wherein:

the p-channel TFT of the driver circuit comprises a channel forming region, a p-type impurity region of a fourth concentration which forms a source region or a drain region and is disposed in contact with the channel forming region;

the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which is disposed in contact with the channel forming region and forms a LDD region that partly overlaps a gate electrode and an n-type impurity region of a third concentration which is disposed on the outside of the n-type impurity region of the first concentration and forms a source region or a drain region;

the pixel TFT comprises a channel forming region, an n-type impurity region of a second concentration which is disposed in contact with the channel forming region and forms a LDD region and an n-type impurity of the third concentration which is disposed on the outside of the n-type impurity region of the second concentration and forms a source region or a drain region;

a pixel electrode disposed in the pixel section has a light reflective surface, the pixel electrode is formed over an interlayer insulating film comprising an organic insulating material and is connected to the pixel TFT through an opening formed in a protective insulating film comprising an inorganic insulating material disposed over a gate electrode of the pixel TFT and in the interlayer insulating film formed in contact with the protective insulating film; and

said one of the substrate is stuck to the other substrate on which a transparent conductive film is formed, through at least a columnar spacer formed on superposition of the opening.

a3
25 (Amended). A semiconductor device according to claim 1 wherein the semiconductor device is in an apparatus selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic game machine and a projector.

a4
27 (Amended). A semiconductor device according to claim 3 wherein the semiconductor device is in an apparatus selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic game machine and a projector.

Please add new claim 53 as follows.

Sub B3 ✓
a5
53. (New) A semiconductor device comprising:
a pixel TFT having disposed in a pixel section over a substrate;
a driver circuit comprising a p-channel TFT and an n-channel TFT over the substrate,
a first interlayer insulating film comprising an inorganic insulating material formed over the pixel section;
a second interlayer insulating film comprising an organic insulating material over the first interlayer insulating film;
a pixel electrode having light reflective surface over the second interlayer insulating film, and in connected to the pixel TFT through an opening formed in the first and second interlayer insulating film;
a source wiring over the second interlayer insulating film;
an alignment film formed over the pixel electrode and the source wiring; and
a liquid crystal interposed between the alignment film and an opposed substrate,

wherein:

the p-channel TFT of the driver circuit comprises a channel forming region and a p-type impurity region of a fourth concentration that forms a source region or a drain region and is disposed in contact with the channel forming region;

the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which forms a LDD region that is disposed in contact with the channel forming region and partly overlaps a gate electrode, and an n-type impurity region of a third concentration which is disposed in the outside of the n-type impurity region of the first concentration and forms a source region or a drain region;

the pixel TFT comprises a channel forming region, an n-type impurity region of a second concentration which is disposed in contact with the channel forming region and forms a LDD region, and an n-type impurity region of the third concentration which is disposed in the outside of the n-type impurity region of the second concentration and forms a source region or a drain region;

the pixel electrode and the source wiring are formed, simultaneously.

REMARKS

Applicants have the following remarks in response to the Office Action:

I. Drawings

The Examiner objects to the drawings as failing to show photoresist masks PM1 and PM6. Applicants have reviewed the application and note that, while these photoresist masks were shown in original Figs. 1C and 3C and discussed in the specification at pages 19 and 28, they were not shown as applied in the drawings. Accordingly, Applicants are revising the drawings to show the